# **Dual Common Cathode Schottky Barrier Diodes**

These Schottky barrier diodes are designed for high speed switching applications, circuit protection, and voltage clamping. Extremely low forward voltage reduces conduction loss. Miniature surface mount package is excellent for hand-held and portable applications where space is limited.

### **Features**

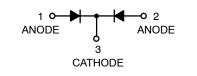
- Extremely Fast Switching Speed
- Low Forward Voltage 0.35 V (Typ) @  $I_F = 10 \text{ mAdc}$
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant



### **ON Semiconductor®**

http://onsemi.com

### **30 VOLT** DUAL COMMON CATHODE SCHOTTKY BARRIER DIODES



C unless otherwise noted)			3 MARKING DIAGRAM
Symbol	Value	Unit	
V <sub>R</sub>	30	V	2 5C M 2
P <sub>F</sub>	225 1.8	mW mW/°C	SOT-23 CASE 318 1
$R_{\thetaJA}$	508 (Note 1) 311 (Note 2)	°C/W	5C = Device Code
١ <sub>F</sub>	200 Max	mA	M = Date Code Pb-Free Package
I <sub>FSM</sub>	600	mA	(Note: Microdot may be in either location) *Date Code orientation and/or position may vary depending upon manufacturing location.
I <sub>FRM</sub>	300	mA	

<b>ORDERING II</b>	NFORMATION
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Device	Package	Shipping <sup>†</sup>
BAT54CLT1G	SOT-23 (Pb-Free)	3000/Tape & Reel
BAT54CLT3G	SOT-23 (Pb-Free)	10,000/Tape & Reel

†For information on tape and reel specifications,

including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

### MAXIMUM RATINGS (T<sub>J</sub> = 125°C

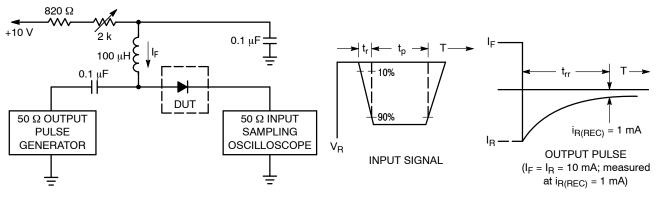
Rating	Symbol	Value	Unit
Reverse Voltage	V <sub>R</sub>	30	V
Forward Power Dissipation @ T <sub>A</sub> = 25°C Derate above 25°C	P <sub>F</sub>	225 1.8	mW mW/°C
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	508 (Note 1) 311 (Note 2)	°C/W
Forward Current (DC)	١ <sub>F</sub>	200 Max	mA
Non-Repetitive Peak Forward Current t <sub>p</sub> < 10 msec	I <sub>FSM</sub>	600	mA
Repetitive Peak Forward Current Pulse Wave = 1 sec, Duty Cycle = 66%	I <sub>FRM</sub>	300	mA
Junction Temperature	Т <sub>Ј</sub>	-55 to +125	°C
Storage Temperature Range	T <sub>stg</sub>	-55 to +150	°C

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

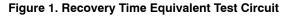
1. FR-4 @ Minimum Pad.

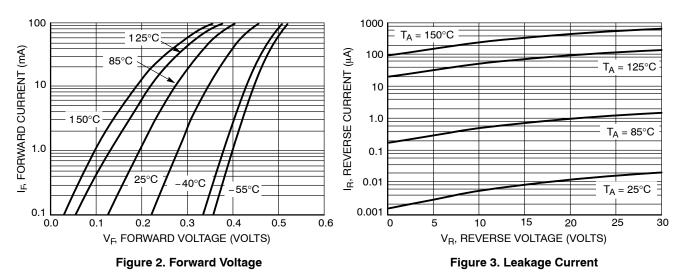
2. FR-4 @ 1.0 x 1.0 inch Pad.

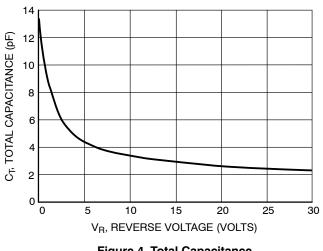
Characteristic	Symbol	Min	Тур	Max	Unit
Reverse Breakdown Voltage (I <sub>R</sub> = 10 µA)	V <sub>(BR)R</sub>	30	-	-	V
Total Capacitance (V <sub>R</sub> = 1.0 V, f = 1.0 MHz)	CT	-	7.6	10	pF
Reverse Leakage (V <sub>R</sub> = 25 V)	۱ <sub>R</sub>	-	0.5	2.0	μA
Forward Voltage (I <sub>F</sub> = 0.1 mAdc)	V <sub>F</sub>	-	0.22	0.24	V
Forward Voltage (I <sub>F</sub> = 30 mAdc)	V <sub>F</sub>	-	0.41	0.5	V
Forward Voltage (I <sub>F</sub> = 100 mAdc)	V <sub>F</sub>	-	0.52	0.8	V
Reverse Recovery Time $(I_F = I_R = 10 \text{ mAdc}, I_{R(REC)} = 1.0 \text{ mAdc}, Figure 1)$	t <sub>rr</sub>	-	-	5.0	ns
Forward Voltage (I <sub>F</sub> = 1.0 mAdc)	V <sub>F</sub>	-	0.29	0.32	V
Forward Voltage (I <sub>F</sub> = 10 mAdc)	V <sub>F</sub>	-	0.35	0.40	V



Notes: 1. A 2.0 k $\Omega$  variable resistor adjusted for a Forward Current (I<sub>F</sub>) of 10 mA. 2. Input pulse is adjusted so  $I_{R(peak)}$  is equal to 10 mA. 3. t<sub>p</sub> » t<sub>rr</sub>

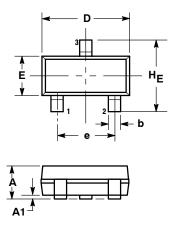


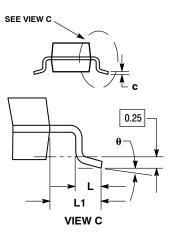




### PACKAGE DIMENSIONS

SOT-23 (TO-236) CASE 318-08 ISSUE AP





NOTES:

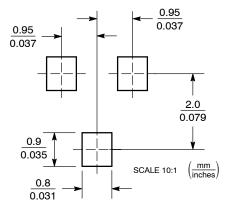
- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
  CONTROLLING DIMENSION: INCH.
  MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH
- MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
- DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

	MILLIMETERS			INCHES			
DIM	MIN	NOM	MAX	MIN	NOM	MAX	
Α	0.89	1.00	1.11	0.035	0.040	0.044	
A1	0.01	0.06	0.10	0.001	0.002	0.004	
b	0.37	0.44	0.50	0.015	0.018	0.020	
c	0.09	0.13	0.18	0.003	0.005	0.007	
D	2.80	2.90	3.04	0.110	0.114	0.120	
Е	1.20	1.30	1.40	0.047	0.051	0.055	
е	1.78	1.90	2.04	0.070	0.075	0.081	
L	0.10	0.20	0.30	0.004	0.008	0.012	
L1	0.35	0.54	0.69	0.014	0.021	0.029	
HE	2.10	2.40	2.64	0.083	0.094	0.104	
θ	0°		10°	0°		10°	

STYLE 9: PIN 1. ANODE 2. ANODE

3. CATHODE

#### SOLDERING FOOTPRINT\*



\*For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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